

Maximum Ratings (@T_A = +25 °C, unless otherwise specified.)

| Characteristic | | Symbol | Value | Units |
|-----------------------------------|--|----------------|--------------|-------|
| Drain-Source Voltage | | V_{DSS} | -20 | V |
| Gate-Source Voltage | | V_{GSS} | ±8 | V |
| Continuous Drain Current (Note 6) | T _A = +25 °C T _A = +85 °C | l _D | -0.9 -0.7 | А |

Thermal Characteristics (@ $T_A = +25$ °C, unless otherwise specified.)

| Characteristic | | Symbol | Value | Units | |
|--|-----------------|-----------------------------------|-------------|-------|--|
| Total Power Dissipation (Note 5) | 0 | 0.45 | W | | |
| Total Power Dissipation (Note 6) | P_{D} | 0.6 | W | | |
| Thermal Resistance, Junction to Ambient (Note 5) | Steady State | | 275 | | |
| Thermal Resistance, Junction to Ambient (Note 6) | Steady State | $R_{\theta JA}$ | 208 | .c∖M | |
| Thermal Resistance, Junction to Case | | $R_{\theta JC}$ | 72 | | |
| Operating and Storage Temperature Range | | T _J , T _{STG} | -55 to +150 | ∞ | |

Electrical Characteristics (@T_A = +25 °C, unless otherwise specified.)

| Characteristic | Symbol | Min | Тур | Max | Unit | Test Condition | |
|-----------------------------------|----------------------|------|-------------------|---------------------|------|---|--|
| OFF CHARACTERISTICS (Note 7) | | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | -20 | _ | _ | V | $V_{GS} = 0V, I_D = 250\mu A$ | |
| Zero Gate Voltage Drain Current | I _{DSS} | _ | | -1 | μΑ | $V_{DS} = -16V, V_{GS} = 0V$ | |
| Gate-Body Leakage | I_{GSS} | | | ±10 | μΑ | $V_{GS} = \pm 8V, V_{DS} = 0V$ | |
| ON CHARACTERISTICS (Note 7) | | | | | | | |
| Gate Threshold Voltage | V _{GS(th)} | -0.4 | _ | -1.2 | V | $V_{DS} = V_{GS}, I_{D} = -250 \mu A$ | |
| Static Drain-Source On-Resistance | R _{DS (ON)} | _ | 180 240 320 | 260 500 1,000 | mΩ | $V_{GS} = -4.5V$, $I_D = -0.88A$ $V_{GS} = -2.5V$, $I_D = -0.71A$ $V_{GS} = -1.8V$, $I_D = -0.20A$ | |
| Diode Forward Voltage | V_{SD} | | -0.8 | -1.2 | V | $V_{GS} = 0V$, $I_{S} = -0.48A$ | |
| DYNAMIC CHARACTERISTICS (Note 8) | | | | | | | |
| Input Capacitance | C _{iss} | _ | 184 | | pF | | |
| Output Capacitance | Coss | _ | 26.4 | | рF | V _{DS} = -10V, V _{GS} = 0V f = 1.0MHz | |
| Reverse Transfer Capacitance | C _{rss} | _ | 18.5 | | рF | | |
| Gate Resistance | R_{g} | | 221 | _ | Ω | $V_{DS} = V_{GS} = 0V, f = 1.0MHz$ | |
| Total Gate Charge | Q_g | | 2.1 | _ | nC | V 45V V 40V | |
| Gate-Source Charge | Q_{gs} | | 0.4 | | nC | $V_{GS} = -4.5V$, $V_{DS} = -10V$, $I_{D} = -1.7A$ | |
| Gate-Drain Charge | Q_{gd} | | 0.5 | _ | nC | | |
| Turn-On Delay Time | t _{D(ON)} | | 9.8 | _ | ns | | |
| Turn-Off Delay Time | t _{D(OFF)} | | 24.4 | _ | ns | $V_{DD} = -10V$, $I_{D} = -1.5A$, | |
| Turn-On Rise Time | t _r | | 88 | _ | ns | $V_{GS} = -4.5V$, $R_{GEN} = 1\Omega$ | |
| Turn-Off Fall Time | t _f | _ | 45 | | ns | | |

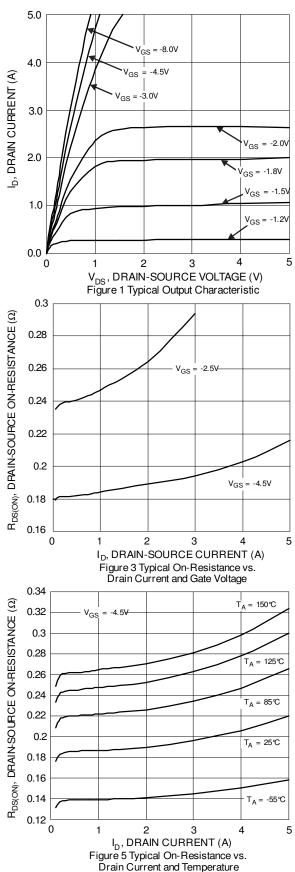
Notes:

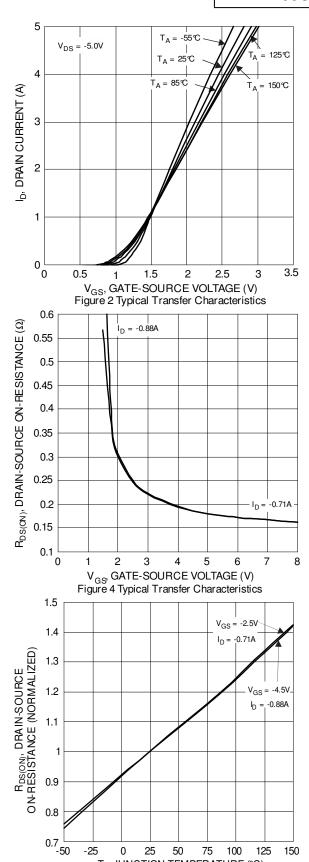
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 Short duration pulse test used to minimize self-heating effect.

- 8. Guaranteed by design. Not subject to product testing.









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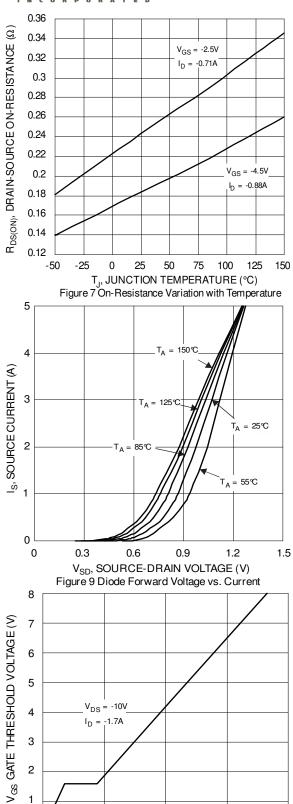
Figure 6 On-Resistance Variation with Temperature

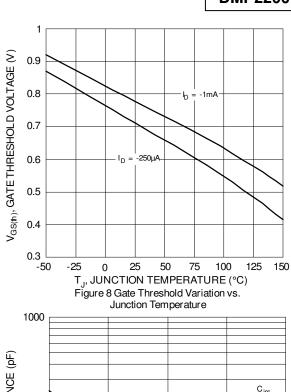
T_J, JUNCTION TEMPERATURE (°C)

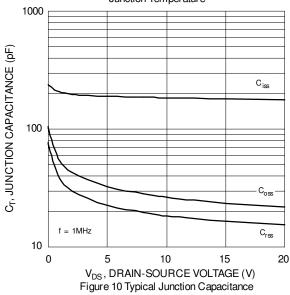
75 100

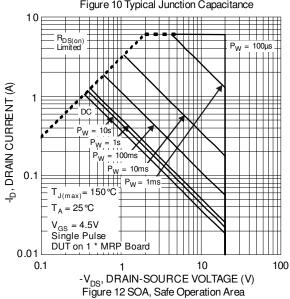












 $Q_{_{\rm G}}$, TOTAL GATE CHARGE (nC)

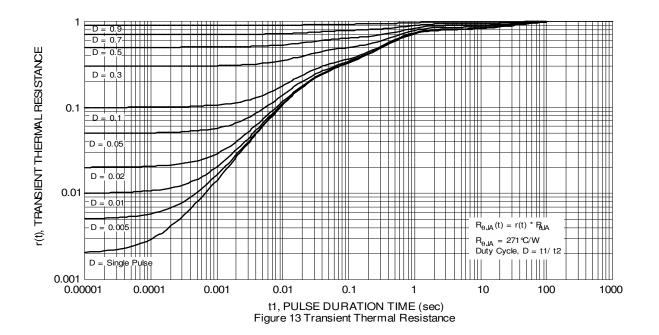
Figure 11 Gate Charge

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0

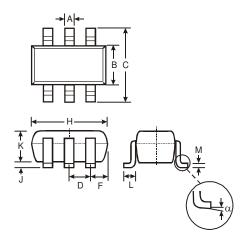
0





Package Outline Dimensions

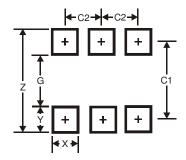
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



| SOT363 | | | | | | |
|----------------------|----------|------|-------|--|--|--|
| Dim | Min | Max | Тур | | | |
| Α | 0.10 | 0.30 | 0.25 | | | |
| В | 1.15 | 1.35 | 1.30 | | | |
| O | 2.00 | 2.20 | 2.10 | | | |
| D | 0.65 Typ | | | | | |
| F | 0.40 | 0.45 | 0.425 | | | |
| Η | 1.80 | 2.20 | 2.15 | | | |
| 7 | 0 | 0.10 | 0.05 | | | |
| K | 0.90 | 1.00 | 1.00 | | | |
| ш | 0.25 | 0.40 | 0.30 | | | |
| М | 0.10 | 0.22 | 0.11 | | | |
| α | 0° | 8° | - | | | |
| All Dimensions in mm | | | | | | |

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



| Dimensions | Value (in mm) | | |
|------------|---------------|--|--|
| Z | 2.5 | | |
| G | 1.3 | | |
| Х | 0.42 | | |
| Υ | 0.6 | | |
| C1 | 1.9 | | |
| C2 | 0.65 | | |



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